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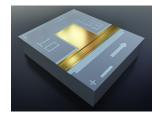
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ML1007

1550 nm Fabry-Pérot Laser Diode for 2.5 Gb/s

Overview

ML1007 is a 1550 nm laser chip with Modulight's proprietary design. The excellent high temperature behaviour of the chip makes it suitable for uncooled transmitters and transceivers up 2.5 Gb/s. The products are shipped as bare dies.



Applications

Communications

SONET/SDH transmitters and transceivers

ATM links

Fiber-in-the-loop

Datacom transceivers

Measurement and instrumentation

Electro-optical Characteristics

Parameter	Symbol	Min	Typical value	Max	Unit	Test condition*
Optical Output Power	P_{OPT}	5	-	-	mW	-40~85°C
Threshold Current	I_{TH}	-	9	14	mA	25°C
	${ m I}_{\sf TH}$	-	23	35	mA	85°C
Operating Current	I_{OP}	-	27	30	mA	25°C, P _{OPT} =5mW
	I_{OP}	-	48	60	mA	85°C, P_{OPT} =5mW
Operating Voltage	V_{OP}	-	1.1	1.4	V	25°C, P _{OPT} =5mW
Slope Efficiency	η	0.22	0.29	-	W/A	25°C, P _{OPT} =5mW, 1-7 mW
	η	0.14	0.19	-	W/A	85°C, P _{OPT} =5mW, 1-7 mW
Peak Wavelength	λ	1530	1550	1570	nm	25°C, P _{OPT} =5mW
	λ	1485	-	1610	nm	-40~85°C, P _{OPT} =5mW
Wavelength Temperature Coefficient	Δλ/ΔΤ	-	0.65	-	nm/K	-40~85°C, P _{OPT} =5mW
Spectral Width (FWHM)**	Δλ	-	1.3	2.5	nm	25°C, P _{OPT} =5mW
Parallel Beam Divergence (FWHM)	θΠ	18	23	35	0	25°C, P _{OPT} =5mW
Perpendicular Beam Divergence (FWHM)	θ⊥	30	44	50	0	25°C, P _{OPT} =5mW
Serial Resistance	R_{S}	-	8	-	Ω	25°C, P _{OPT} =5mW, 1-7 mW
Modulation bandwidth ***	f _{-3dB}	6	-	-	GHz	25 °C, $I_{OP}=I_{TH}+16$ mA
	f_{-3dB}	4	-	-	GHz	$25^{\circ}\text{C}, \ I_{\text{OP}}\text{=}I_{\text{TH}}\text{+}16\text{mA}$

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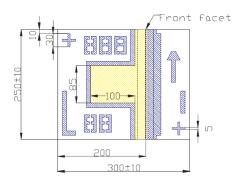


* All temperatures refer to heatsink temperature

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Optical Output Power	P _{OPT}	20	mW
LD reverse voltage	V_{RLD}	2	V
LD forward current	${ m I}_{\sf FLD}$	200	mA
Operating temperature range	T _{OP}	-40~85	°C
Storage temperature range	T _S	-40~85	°C

Mechanical Specification



All dimensions in microns Chip thickness 100 µm Polarity: p-contact (anode) up

Safety Information

- The laser light emitted from this laser diode is invisible and potentially harmful to the human eye. Avoid eye and skin exposure to the beam, both direct and reflected.
- Products are subject to the risks normally associated with sensitive electronic devices including static discharge, transients, and overload. Please ensure ESD protection prior to handling the products.
- These Modulight products are not intended for use in systems where product malfunction can reasonably be expected to result in personal injury.



Peak power and wavelength are for safety analysis only, not to present device performance.

Liability note

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^{** -20} dB noise floor

^{***} Chip-on carrier, ground-signal-ground microwave probe